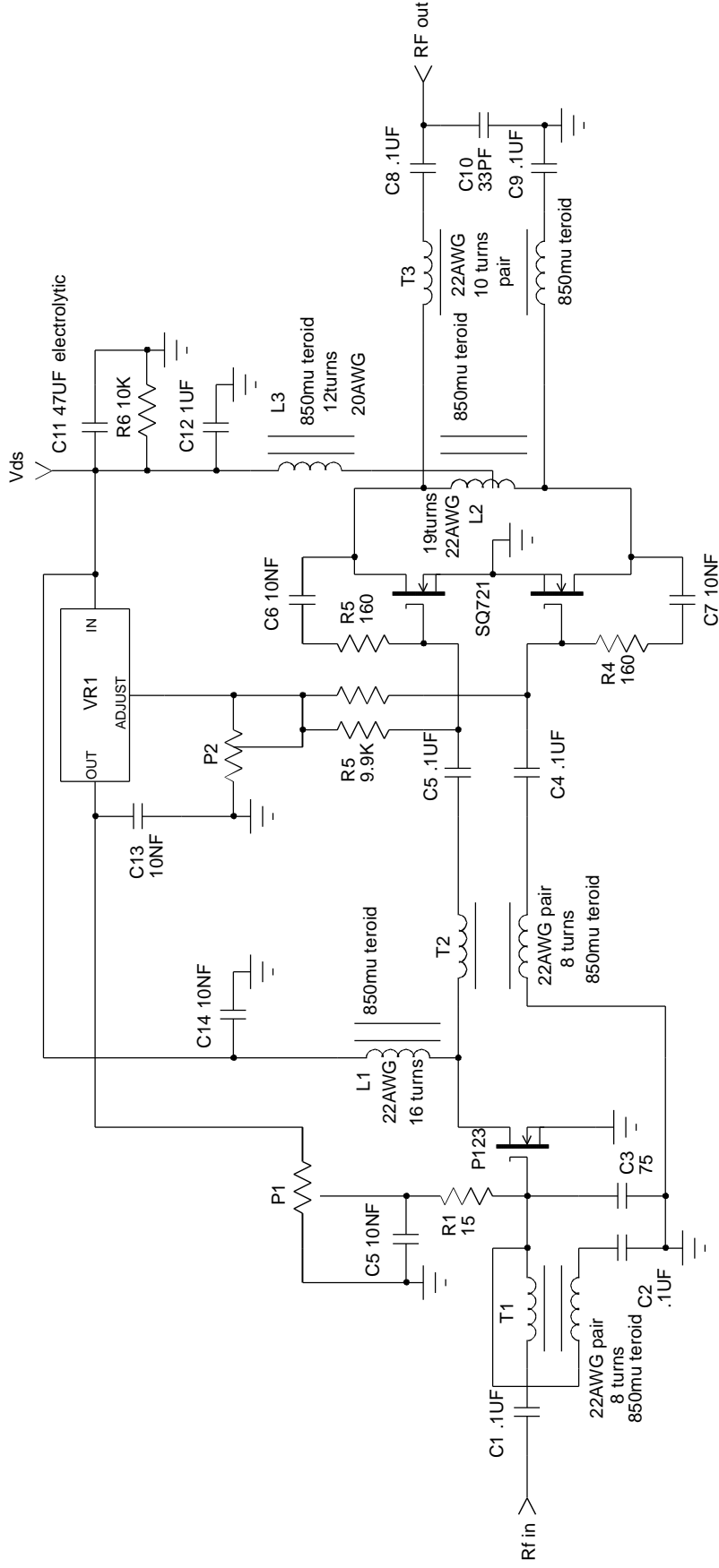
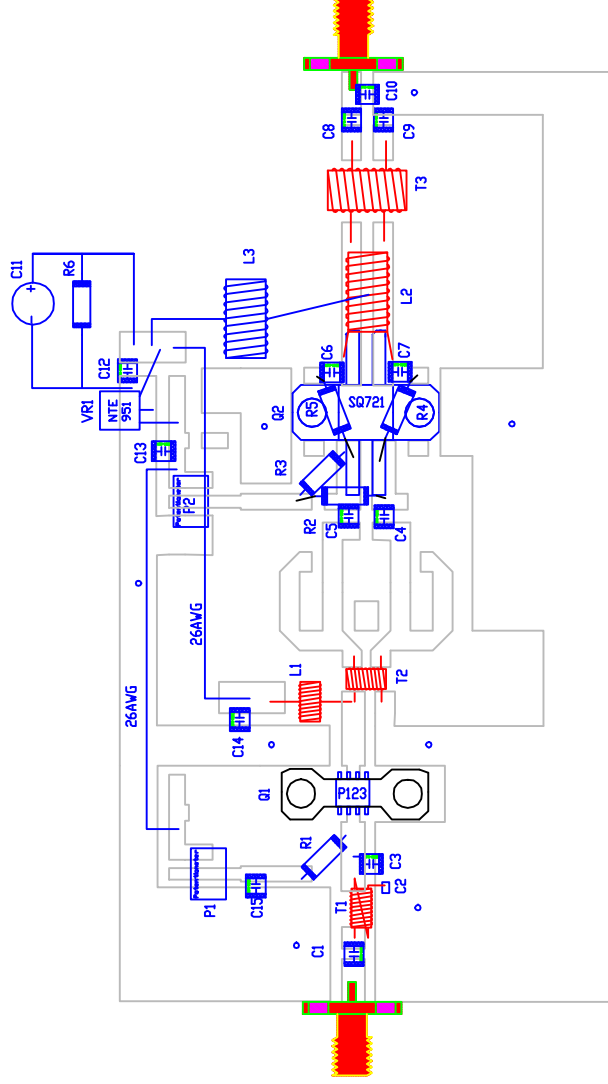


TB111\_A 10-110Mhz\*25dB



DRN BY	J.Citrolo	12/2/03
CHKD	J.Citrolo	12/2/03
ELECT	J.Citrolo	12/2/03
MECH		
PRDC		
QUAL		
PGMS		
Polyfet RF Devices		
<b>Tb111-A, 10-110MHz, 10W, 25dB</b>		
SIZE	FSCM NO.	REV
	P123->SQ721	Vds=12.5Vdc Idq=6A



SYMBOL	VALUE	DESCRIPTION
C1,2,4,5,8,9	.1uf	ATC200B CHIP CAP.
C3	75pf	ATC100B CHIP CAP.
C10	33pf	ATC100B CHIP CAP.
C11	47uf	63V electrolytic
C12	1uf	50V Tantalum
C6,7,13,15	.01uf	ATC200B CHIP CAP.
R1	15	1/4W axial resistor
R2,3,6	9.9K	1/4W axial resistor
R4,5	160	1/4W axial resistor
P01,2	10k	Multi-turn POT
L01	22AWG	850mu toroid 16 turns
L02	22AWG	850mu,center-tap,19 turns
L03	20AWG	850mu, 12 turns
VR1	8V	Voltage regulator
T01,T02	22AWG	850mu toroid 8turns twisted pair
T03	22AWG	850mu toroid 10turns twisted pair
Q1	P123	Polyfet Transistor
Q2	SQ721	Polyfet Transistor

DRN BY: J.Citrolo	12/2/03	POLYFET RF DEVICES	
CHKD :		TB111-A 10-110MHz, 10W 25dB	
ELECT : J Citrolo		SIZE	FSCM NO
MECH : J Citrolo		P123-->SQ721 Vds=125Vdc, Idq=6A	
PROC :		QUAL :	REV
PGMS :		SCALE : 1 : 1	SHEET 1 OF 1

PCB Material : Double Side FR4  
 ER=3.55, H=0.032", T=0.001"